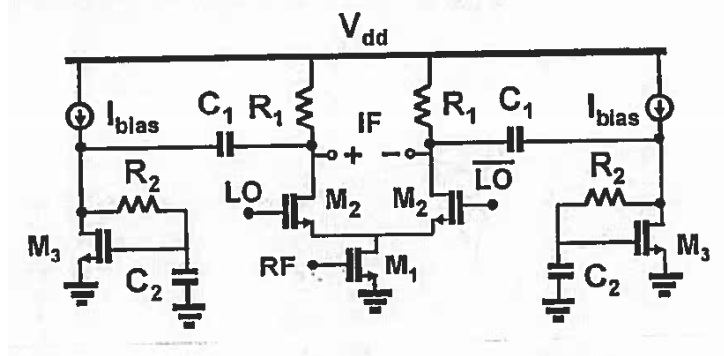


## Tutorial T12

**T12.1** Let us consider the down-conversion mixer in figure and assume that the MOSFETs have threshold  $V_T = 0.5V$ , constant  $1/2\mu C_{OX} = 0.2mA/V^2$  and thermal noise coefficients  $\gamma = 2/3$  and  $\alpha = 1$ . Let  $V_{dd} = 2.5V$ ,  $(W/L)_1 = 125$ ,  $(W/L)_2 = 400$ ,  $R_1 = 200\Omega$ ,  $R_2 = 150\Omega$ ,  $I_{bias} = 6mA$ ,  $C_2 = 1pF$ ,  $(W/L)_3 = 750$ .

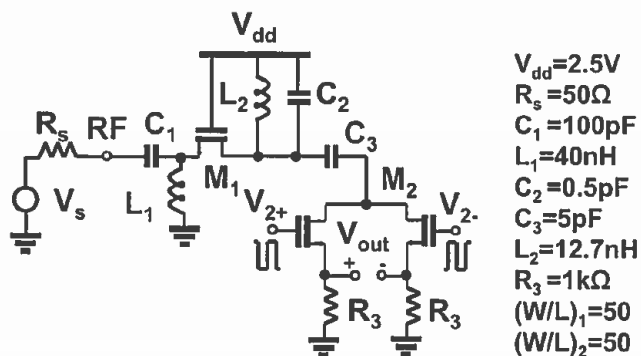
- Set the value of  $C_1$  which guarantees a resonance frequency ( $f_0$ ) of 2GHz for the output network ( $R_2$ ,  $C_1$ ,  $C_2$  and  $M_3$ ).
- Let us assume a sinusoidal wave with offset voltage of 1V and frequency  $f_{RF} = 10GHz$  at the RF port, a square wave with offset voltage of 1.5V, single-ended zero-peak amplitude of 300mV, with frequency  $f_{LO} = 8GHz$ , at the LO port. Compute the conversion gain from RF to IF.
- Consider now  $f_{RF} = f_{LO} = 8GHz$ . Compute the noise figure of the mixer considering all the noise sources, referred to a source resistance of  $R_S = 50\Omega$  and assuming abrupt switching of the M2 pair.



[Sol. a)  $C_1 = 2.5pF$ , b)  $A_v = -12dB$ , c)  $NF = 4.91 dB$ ]

**T12.2** Let  $V_s$  be a sinusoid at  $f_{RF} = 2.0GHz$ , and  $V_{2+}$  and  $V_{2-}$  two square-waves  $0 - V_{dd}$  at  $f_{LO} = 2.1GHz$ . The MOSFETs have threshold  $V_T = 0.5V$ , constant  $1/2\mu C_{OX} = 0.1mA/V^2$  and thermal noise coefficients  $\gamma = 2/3$  and  $\alpha = 1$ .

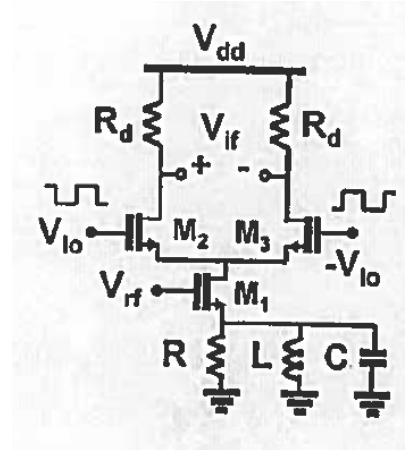
- Derive the bias point of the circuit. Evaluate the RF to IF conversion gain from the input  $V_{rf}$  to the output port  $V_{out}$ .
- Calculate the power gain from the RF port to output port.
- Compute the noise figure of the circuit referred to source resistance  $R_s$ , considering just the thermal noise of M1 and  $R_s$ .



$V_{dd}=2.5V$   
 $R_s=50\Omega$   
 $C_1=100pF$   
 $L_1=40nH$   
 $C_2=0.5pF$   
 $C_3=5pF$   
 $L_2=12.7nH$   
 $R_3=1k\Omega$   
 $(W/L)_1=50$   
 $(W/L)_2=50$

[Sol. a)  $A_v = 22dB$ , b)  $G_p = 6dB$ , c)  $NF = 2.2dB$ ].

**T12.3** Let us consider the mixer in figure, where  $V_{dd} = 2.5V$ ,  $R_d = 200\Omega$ . Let us assume that the MOSFETs have threshold  $V_T = 0.5V$ , constant  $1/2\mu C_{ox} = 0.2mA/V^2$ , and  $V_{rf}$  is a sinusoid with offset voltage of 1V. Let the impedance of the RLC network have its resonance frequency around the image frequency at  $f_{IM} = (f_{LO} - f_{IF})$ .



- Derive the mathematical expression of the image rejection ratio of the stage, computing the ratio between the conversion gain of an input RF signal at  $f_{RF} = (f_{LO} + f_{IF})$  and the conversion gain of an input RF signal at  $f_{IM}$ .
- Size  $(W/L)_1$  and  $R$  to get IIR equal to 30dB and conversion gain at  $f_{RF}$  equal to 10dB.

**[Sol. a)  $IRR = (1+g_{m1}R)$ ; b)  $(W/L)_1 = 124$ ,  $R = 1.2k\Omega$ ]**